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#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Obsolete
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	CANbus, I <sup>2</sup> C, IEBus, SIO, UART/USART
Peripherals	DMA, WDT
Number of I/O	111
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	31K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	128-LQFP
Supplier Device Package	128-LFQFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m306nnfjgp-u3

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# M16C/6N Group (M16C/6NL, M16C/6NN)

Renesas MCU

REJ03B0061-0210 Rev.2.10 Aug 25, 2006

## 1. Overview

The M16C/6N Group (M16C/6NL, M16C/6NN) of MCUs are built using the high-performance silicon gate CMOS process using the M16C/60 Series CPU core and are packaged in 100-pin and 128-pin plastic molded LQFP. These MCUs operate using sophisticated instructions featuring a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed. Being equipped with one CAN (Controller Area Network) module in the M16C/6N Group (M16C/6NL, M16C/6NN), the MCU is suited to drive automotive and industrial control systems. The CAN module complies with the 2.0B specification. In addition, this MCU contains a multiplier and DMAC which combined with fast instruction processing capability, makes it suitable for control of various OA, communication equipment which requires high-speed arithmetic/logic operations.

## **1.1 Applications**

· Car audio and industrial control systems, other

Specifications written in this manual are believed to be accurate, but are not guaranteed to be entirely free of error. Specifications in this manual may be changed for functional or performance improvements. Please make sure your manual is the latest edition.



## **1.2 Performance Overview**

Tables 1.1 and 1.2 list the Functions and Specifications for M16C/6N Group (M16C/6NL, M16C/6NN).

Item			Specification			
CPU	Number of fund	damental	91 instructions			
	instructions					
	Minimum instruction	on execution time	41.7ns (f(BCLK) = 24 MHz, 1/1 prescaler, without software wait			
	Operating mode		Single-chip, memory expansion and microprocessor modes			
	Address space	)	1 Mbyte			
	Memory capacity		Refer to Table 1.3 Product Information			
Peripheral	Ports		Input/Output: 87 pins, Input: 1 pin			
Function	Multifunction tir	ners	Timer A: 16 bits $\times$ 5 channels			
			Timer B: 16 bits $\times$ 6 channels			
			Three-phase motor control circuit			
	Serial interface	es	3 channels			
			Clock synchronous, UART, I <sup>2</sup> C-bus <sup>(1)</sup> , IEBus <sup>(2)</sup>			
			2 channels			
			Clock synchronous			
	A/D converter		10-bit A/D converter: 1 circuit, 26 channels			
	D/A converter		8 bits $\times$ 2 channels			
	DMAC		2 channels			
	CRC calculation circuit		CRC-CCITT			
	CAN module		1 channel with 2.0B specification			
	Watchdog timer		15 bits $\times$ 1 channel (with prescaler)			
	Interrupts		Internal: 30 sources, External: 9 sources			
			Software: 4 sources, Priority levels: 7 levels			
	Clock generati	on circuits	4 circuits			
			Main clock oscillation circuit (*)			
			Sub clock oscillation circuit (*)			
			On-chip oscillator			
			PLL frequency synthesizer			
			(*) Equipped with on-chip feedback resistor			
	Oscillation-stop	ped detector	Main clock oscillation stop and re-oscillation detection function			
Electrical	Supply voltage	•	VCC = 3.0 to 5.5 V			
Characteristics			(f(BCLK) = 24 MHz, 1/1 prescaler, without software wait)			
	Consumption	Mask ROM	19mA (f(BCLK) = 24 MHz, PLL operation, no division)			
	current	Flash memory	21mA (f(BCLK) = 24 MHz, PLL operation, no division)			
		Mask ROM	3µA (f(BCLK) = 32 kHz, Wait mode, Oscillation capacity Low)			
		Flash memory	0.8µA (Stop mode, Topr = 25°C)			
Flash Memory	Programming and	erasure voltage	$3.3 \pm 0.3$ V or $5.0 \pm 0.5$ V			
Version	Programming and e					
I/O	I/O withstand v		5.0 V			
Characteristics	Output current		5m A			
	bient Tempera		-40 to 85°C			
Device Config	guration		CMOS high-performance silicon gate			
Package			100-pin molded-plastic LQFP			
			, . ,			

NOTES:

1. I<sup>2</sup>C-bus is a trademark of Koninklijke Philips Electronics N.V.

2. IEBus is a trademark of NEC Electronics Corporation.

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	CAN Module Pin	Pin
51		P5_6						ALE
52		P5_5						HOLD
53		P5_4						HLDA
54		P13_3						
55		P13_2						
56		P13_1						
57		P13_0						
58		P5_3						BCLK
59		P5_2						RD
60		P5_1						WRH/BHE
61		P5_0						WRL/WR
62		P12_7						
63		P12_6						
64		P12_5						
65		P4_7						CS3
66		 P4_6						CS2
67		 P4_5						CS1
68		P4_4						<u>CS0</u>
69		P4_3						A19
70		P4_2						A18
71		P4_1						A17
72		P4_0						A16
73		P3_7						A15
74		P3_6						A14
75		P3_5						A13
76		P3_4						A12
77		P3_3						A11
78		P3_2						A10
79		P3_1						A9
80		P12_4						7.5
81		P12_3						
82		P12_2						
83		P12_1						
84		P12_0						
85	VCC2	1 12_0						
86	1002	P3_0						A8(/-/D7)
87	vss	1.5_0						70(/7/07)
88	1000	P2_7				AN2_7		A7(/D7/D6)
89		P2_7				AN2_7 AN2_6		A6(/D6/D5)
90		P2_0 P2_5				AN2_6		A5(/D5/D4)
90		P2_5				AN2_3		A3(/D3/D4) A4(/D4/D3)
91		P2_4				AN2_4		A4(/D4/D3) A3(/D3/D2)
92		P2_3 P2_2				AN2_3		A3(/D3/D2) A2(/D2/D1)
93		P2_2 P2_1				AN2_2 AN2_1		A1(/D1/D0)
94 95								A0(/D0/-)
95 96		P2_0 P1_7	INT5			AN2_0		D15
			INT5 INT4					D15 D14
97		P1_6	INT3					D14 D13
98 99		P1_5	11113					D13 D12
99 100		P1_4 P1_3						D12 D11

## 1.6 Pin Functions

Tables 1.9 to 1.11 list the Pin Functions.

Signal Name	Pin Name	I/O Type	Description
Power supply	VCC1, VCC2,	I	Apply 3.0 to 5.5 V to the VCC1 and VCC2 pins and 0 V to the VSS
input	VSS		pin. The VCC apply condition is that VCC2 = VCC1 $^{(1)}$ .
Analog power	AVCC, AVSS		Applies the power supply for the A/D converter. Connect the AVCC
supply input	,		pin to VCC1. Connect the AVSS pin to VSS.
Reset input	RESET		The MCU is in a reset state when applying "L" to the this pin.
CNVSS	CNVSS		Switches processor mode. Connect this pin to VSS to when after
			a reset to start up in single-chip mode. Connect this pin to VCC1
			to start up in microprocessor mode.
External data	BYTE	1	Switches the data bus in external memory space. The data bus
bus width			is 16-bit long when the this pin is held "L" and 8-bit long when
select input			the this pin is held "H". Set it to either one. Connect this pin to
Select Input			VSS when single-chip mode.
Bus control	D0 to D7	I/O	Inputs and outputs data (D0 to D7) when these pins are set as
		1/0	the separate bus.
pins		1/0	· · ·
	D8 to D15	I/O	Inputs and outputs data (D8 to D15) when external 16-bit data
			bus is set as the separate bus.
	A0 to A19	0	Output address bits (A0 to A19).
	A0/D0 to A7/D7	I/O	Input and output data (D0 to D7) and output address bits (A0 to
			A7) by time-sharing when external 8-bit data bus are set as the
			multiplexed bus.
	A1/D0 to A8/D7	I/O	Input and output data (D0 to D7) and output address bits (A1 to
			A8) by time-sharing when external 16-bit data bus are set as the
			multiplexed bus.
	CS0 to CS3	0	Output $\overline{CS0}$ to $\overline{CS3}$ signals. $\overline{CS0}$ to $\overline{CS3}$ are chip-select signals
			to specify an external space.
	WRL/WR	0	Output WRL, WRH, (WR, BHE), RD signals. WRL and WRH or
	WRH/BHE		BHE, and WR can be switched by program.
	RD		<ul> <li>WRL, WRH, and RD are selected</li> </ul>
			The WRL signal becomes "L" by writing data to an even address
			in an external memory space.
			The WRH signal becomes "L" by writing data to an odd address
			in an external memory space.
			The RD pin signal becomes "L" by reading data in an external
			memory space.
			• WR, BHE, and RD are selected
			The WR signal becomes "L" by writing data in an external
			memory space.
			The RD signal becomes "L" by reading data in an external
			memory space.
			The BHE signal becomes "L" by accessing an odd address.
			Select WR, BHE, and RD for an external 8-bit data bus.
		0	ALE is a signal to latch the address.
	ALE	0	While the HOLD pin is held "L", the MCU is placed in a hold
	HOLD	I	
			state.
	HLDA	0	In a hold state, HLDA outputs a "L" signal.
	RDY		While applying a "L" signal to the RDY pin, the MCU is placed in
	 : Output I/O: Ir	  put/Outpu	a wait state.

## Table 1.9 Pin Functions (100-pin and 128-pin Versions) (1)

I: Input O: Output I/O: Input/Output

NOTE:

1. In this manual, hereafter, VCC refers to VCC1 unless otherwise noted.

RENESAS

1. Overview

## Table 1.10 Pin Functions (100-pin and 128-pin Versions) (2)

Signal Name	Pin Name	I/O Type	
Main clock	XIN	I	I/O pins for the main clock oscillation circuit. Connect a ceramic
input			resonator or crystal oscillator between XIN and XOUT <sup>(1)</sup> .
Main clock	XOUT	0	To use the external clock, input the clock from XIN and leave
output			XOUT open.
Sub clock	XCIN	I	I/O pins for a sub clock oscillation circuit. Connect a crysta
input			oscillator between XCIN and XCOUT <sup>(1)</sup> .
Sub clock	XCOUT	0	To use the external clock, input the clock from XCIN and leave
output			XCOUT open.
BCLK output	BCLK	0	Outputs the BCLK signal.
Clock output	CLKOUT	0	The clock of the same cycle as fC, f8, or f32 is output.
INT interrupt input	NT0 to INT8 (2)	I	Input pins for the INT interrupt.
NMI interrupt	NMI	I	Input pin for the NMI interrupt.
input			
Key input	KI0 to KI3	I	Input pins for the key input interrupt.
interrupt input			
Timer A	TA0OUT to TA4OUT	I/O	These are timer A0 to timer A4 I/O pins.
	TA0IN to TA4IN	I	These are timer A0 to timer A4 input pins.
	ZP	I	Input pin for the Z-phase.
Timer B	TB0IN to TB5IN		These are timer B0 to timer B5 input pins.
Three-phase motor	$\overline{U, \overline{U}, V, \overline{V}, W, \overline{W}}$	0	These are Three-phase motor control output pins.
control output			
Serial interface	CTS0 to CTS2	I	These are transmit control input pins.
	RTS0 to RTS2	0	These are receive control output pins.
	CLK0 to CLK6 <sup>(2)</sup>	I/O	These are transfer clock I/O pins.
	RXD0 to RXD2	I	These are serial data input pins.
	SIN3 to SIN6 (2)	I	These are serial data input pins.
	TXD0 to TXD2	0	These are serial data output pins.
	SOUT3 to SOUT6 (2)	0	These are serial data output pins.
	CLKS1	0	This is output pin for transfer clock output from multiple pins
			function.
I <sup>2</sup> C mode	SDA0 to SDA2	I/O	These are serial data I/O pins.
	SCL0 to SCL2	I/O	These are transfer clock I/O pins. (however, SCL2 for
			the N-channel open drain output.)
Reference	VREF	I	Applies the reference voltage for the A/D converter and D/A
voltage input			converter.
A/D converter	AN0 to AN7		Analog input pins for the A/D converter.
	AN0_0 to AN0_7		
	AN2_0 to AN2_7		
	ADTRG		This is an A/D trigger input pin.
	ANEX0	I/O	This is the extended analog input pin for the A/D converter
			and is the output in external op-amp connection mode.
	ANEX1		This is the extended analog input pin for the A/D converter.
D/A converter	DA0, DA1	0	These are the output pins for the D/A converter.
CAN module	CRX0		This is the input pin for the CAN module.
	СТХО	0	This is the output pin for the CAN module.
: Input O:		put/Outpu	

I: Input O: Output I/O: Input/Output

#### NOTES:

1. Ask the oscillator maker the oscillation characteristic.

2. INT6 to INT8, CLK5, CLK6, SIN5, SIN6, SOUT5, SOUT6 are only in the 128-pin version.

## Table 4.4 SFR Information (4)

Address	Register	Symbol	After Reset
00C0h			XXh
00C1h			XXh
00C2h	CAN0 Message Box 6: Identifier / DLC		XXh
00C3h			XXh
00C4h			XXh
00C5h			XXh XXh
00C6h 00C7h			XXh
00C7h 00C8h			XXh
00C9h	CANO Massage Day & Data Field		XXh
00CAh	CAN0 Message Box 6: Data Field		XXh
00CBh			XXh
00CCh			XXh
00CDh			XXh
00CEh	CAN0 Message Box 6: Time Stamp		XXh
00CFh 00D0h			XXh XXh
00D0h			XXh
00D1h 00D2h			XXh
00D2h	CAN0 Message Box 7: Identifier / DLC		XXh
00D4h			XXh
00D5h			XXh
00D6h			XXh
00D7h			XXh
00D8h			XXh
00D9h	CAN0 Message Box 7: Data Field		XXh XXh
00DAh 00DBh			XXn XXh
00DBh 00DCh			XXh
00DDh			XXh
00DEh	CANO Massage Day 7: Time Otoma		XXh
00DFh	CAN0 Message Box 7: Time Stamp		XXh
00E0h			XXh
00E1h			XXh
00E2h	CAN0 Message Box 8: Identifier / DLC		XXh
00E3h	-		XXh XXh
00E4h 00E5h			XXh
00E5h			XXh
00E7h			XXh
00E8h			XXh
00E9h	CAN0 Message Box 8: Data Field		XXh
00EAh	Or the message box o. Data Fleid		XXh
00EBh			XXh
00ECh			XXh
00EDh 00EEh			XXh XXh
00EEh	CAN0 Message Box 8: Time Stamp		XXh
00E111			XXh
00F1h			XXh
00F2h	CANO Massaga Bax 0: Identifiar / DI C		XXh
00F3h	CAN0 Message Box 9: Identifier / DLC		XXh
00F4h			XXh
00F5h			XXh
00F6h			XXh
00F7h			XXh XXh
00F8h 00F9h			XXh
00F9h	CAN0 Message Box 9: Data Field		XXh
00FBh			XXh
00FCh			XXh
00FDh			XXh
00FEh	CAN0 Message Box 9: Time Stamp		XXh
00FFh			XXh

X: Undefined



## Table 4.7 SFR Information (7) (2)

Address	Register	Symbol	After Reset
0180h	×	· ·	
0181h			
0182h			
0183h			
0184h			
0185h			
0186h			
0187h			
0188h 0189h			
018Ah			
018Bh			
018Ch			
018Dh			
018Eh			
018Fh			
0190h			
0191h			
0192h			
0193h			
0194h 0195h			
0195h			
0197h			
0198h			
0199h			
019Ah			
019Bh			
019Ch			
019Dh			
019Eh 019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h 01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h 01B2h			
01B2h 01B3h			
01B3n			
01B5h	Flash Memory Control Register 1 (1)	FMR1	0X00XX0Xb
01B6h			
01B7h	Flash Memory Control Register 0 <sup>(1)</sup>	FMR0	0000001b
01B8h			00h
01B9h	Address Match Interrupt Register 2	RMAD2	00h
01BAh	Address Match Islands Frankla Davida A		X0h
01BBh	Address Match Interrupt Enable Register 2	AIER2	XXXXXX00b
01BCh 01BDh	Address Match Interrupt Register 3	RMAD3	00h 00h
01BDh 01BEh	Auress maith interrupt negister s	NIVIAD3	X0h
01BFh			700
X: Undefine		1	ı I

X: Undefined

NOTES:

These registers are included in the flash memory version. Cannot be accessed by users in the mask ROM version.
 Blank spaces are reserved. No access is allowed.



## Table 4.8 SFR Information (8) <sup>(3)</sup>

Address	Register	Symbol	After Reset
01C0h	Timer B3, B4, B5 Count Start Flag	TBSR	000XXXXXb
01C0n	Timer B3, B4, B5 Count Start Flag	IBSR	000/////
			XXh
01C2h	Timer A1-1 Register	TA11	XXh
01C3h	-		XXh
01C4h	Timer A2-1 Register	TA21	XXh
01C5h			XXh
01C6h	Timer A4-1 Register	TA41	XXh
01C7h			
01C8h	Three-Phase PWM Control Register 0	INVC0 INVC1	00h
01C9h	Three-Phase PWM Control Register 1 Three-Phase Output Buffer Register 0	IDB0	00h
01CAh			00111111b
01CBh	Three-Phase Output Buffer Register 1 Dead Time Timer	IDB1	00111111b
01CCh		DTT	XXh
01CDh	Timer B2 Interrupt Generation Frequency Set Counter	ICTB2	XXh
01CEh	Laterary October Designer O	15050	Vaaaaaa
01CFh	Interrupt Source Select Register 2	IFSR2	X000000b
01D0h	Timer B3 Register	ТВЗ	XXh
01D1h			XXh
01D2h	Timer B4 Register	ТВ4	XXh
01D3h	5		XXh
01D4h	Timer B5 Register	ТВ5	XXh
01D5h			XXh
01D6h	SI/O6 Transmit/Receive Register (1)	S6TRR	XXh
01D7h			01000000
01D8h	SI/O6 Control Register <sup>(1)</sup>	S6C	0100000b
01D9h	SI/O6 Bit Rate Register <sup>(1)</sup>	S6BRG	XXh
01DAh	SI/O3, 4, 5, 6 Transmit/Receive Register <sup>(2)</sup>	S3456TRR	XXXX0000b
01DBh	Timer B3 Mode Register	TB3MR	00XX0000b
01DCh	Timer B4 Mode Register	TB4MR	00XX0000b
01DDh	Timer B5 Mode Register	TB5MR	00XX0000b
01DEh	Interrupt Source Select Register 0	IFSR0	00h
01DFh	Interrupt Source Select Register 1	IFSR1	00h
01E0h	SI/O3 Transmit/Receive Register	S3TRR	XXh
01E1h			
01E2h	SI/O3 Control Register	S3C	0100000b
01E3h	SI/O3 Bit Rate Register	S3BRG	XXh
01E4h	SI/O4 Transmit/Receive Register	S4TRR	XXh
01E5h			
01E6h	SI/O4 Control Register	S4C	0100000b
01E7h	SI/O4 Bit Rate Register	S4BRG	XXh
01E8h	SI/O5 Transmit/Receive Register (1)	S5TRR	XXh
01E9h			
01EAh	SI/O5 Control Register <sup>(1)</sup>	S5C	0100000b
01EBh	SI/O5 Bit Rate Register <sup>(1)</sup>	S5BRG	XXh
01ECh	UARTO Special Mode Register 4	U0SMR4	00h
01EDh	UARTO Special Mode Register 3	U0SMR3	000X0X0Xb
01EEh	UART0 Special Mode Register 2	U0SMR2	X000000b
01EFh	UART0 Special Mode Register	U0SMR	X000000b
01F0h	UART1 Special Mode Register 4	U1SMR4	00h
01F1h	UART1 Special Mode Register 3	U1SMR3	000X0X0Xb
01F2h	UART1 Special Mode Register 2	U1SMR2	X000000b
01F3h	UART1 Special Mode Register	U1SMR	X000000b
01F4h	UART2 Special Mode Register 4	U2SMR4	00h
01F5h	UART2 Special Mode Register 3	U2SMR3	000X0X0Xb
01F6h	UART2 Special Mode Register 2	U2SMR2	X000000b
01F7h	UART2 Special Mode Register	U2SMR	X000000b
01F8h	UART2 Transmit/Receive Mode Register	U2MR	00h
01F9h	UART2 Bit Rate Register	U2BRG	XXh
01FAh	UART2 Transmit Buffer Register	U2TB	XXh
01FBh	UALTZ HANSINIL DUNEL NEYISLEN	0210	XXh
01FCh	UART2 Transmit/Receive Control Register 0	U2C0	00001000b
01FDh	UART2 Transmit/Receive Control Register 1	U2C1	00000010b
01FEh	LIARTO Receive Ruffer Register		XXh
01FFh	UART2 Receive Buffer Register	U2RB	XXh
V: Undofin		•	

X: Undefined

NOTES:

These registers exist only in the 128-pin version.
 Bits S5TRF and S6TRF in the S3456TRR register are used in the 128-pin version.
 Blank spaces are reserved. No access is allowed.

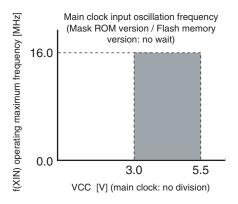


## Table 5.3 Recommended Operating Conditions (2) (1)

Sumbol	Parameter					Unit		
Symbol					Min.	Тур.	Max.	Unit
f(XIN)	Main clock input oscillation	Main clock input oscillation No wait Mask ROM version VCC = 3.0 to 5.5 V						MHz
	frequency (2) (3) (4)	frequency (2) (3) (4) Flash memory version						
f(XCIN)	Sub clock oscillation fre	Sub clock oscillation frequency						kHz
f(Ring)	On-chip oscillation frequencies	On-chip oscillation frequency						MHz
f(PLL)	PLL clock oscillation frequency						24	MHz
f(BCLK)	CPU operation clock VCC = 3.0 to 5.5 V						24	MHz
tsu(PLL)	PLL frequency synthesi	zer stab	ilization wait time				20	ms

NOTES:

- 1. Referenced to VCC = 3.0 to 5.5 V at Topr = -40 to 85°C unless otherwise specified.
- 2. Relationship between main clock oscillation frequency and supply voltage is shown right.
- 3. Execute program/erase of flash memory by VCC = 3.3  $\pm$  0.3 V or VCC = 5.0  $\pm$  0.5 V.
- 4. When using 16 MHz and over, use PLL clock. PLL clock oscillation frequency which can be used is 16 MHz, 20 MHz or 24 MHz.





Symbol	Parameter		Measuring Condition		Standard			Unit
Symbol	Falali	letei				Тур.	Max.	Unit
_	Resolution		VREF :	VREF = VCC			10	Bit
INL	Integral	10 bits	VREF	ANEX0, ANEX1 input, AN0 to AN7 input,			±3	LSB
	nonlinearity		= VCC	AN0_0 to AN0_7 input, AN2_0 to AN2_7 input				
	error		= 5 V	External operation amp connection mode			±7	LSB
			VREF	ANEX0, ANEX1 input, AN0 to AN7 input,			±5	LSB
			= VCC	AN0_0 to AN0_7 input, AN2_0 to AN2_7 input				
			= 3.3 V	External operation amp connection mode			±7	LSB
		8 bits	VREF :	= AVCC = VCC = 3.3 V			±2	LSB
_	Absolute	10 bits	VREF	ANEX0, ANEX1 input, AN0 to AN7 input,			±3	LSB
	accuracy		= VCC	AN0_0 to AN0_7 input, AN2_0 to AN2_7 input				
			= 5 V	External operation amp connection mode			±7	LSB
			VREF	ANEX0, ANEX1 input, AN0 to AN7 input,			±5	LSB
			= VCC	AN0_0 to AN0_7 input, AN2_0 to AN2_7 input				
			= 3.3 V	External operation amp connection mode			±7	LSB
		8 bits	VREF :	= AVCC = VCC = 3.3 V			±2	LSB
DNL	Differential non	linearity error					±1	LSB
-	Offset error						±3	LSB
-	Gain error						±3	LSB
RLADDER	Resistor ladde	r	VREF :	= VCC	10		40	kΩ
tconv	10-bit conversi	on time,	VREF :	= VCC = 5 V, φAD = 10 MHz	3.3			μs
	sample & hold available							
	8-bit conversion time,		VREF :	= VCC = 5 V,	2.8			μs
	sample & hold available							
<b>t</b> SAMP	Sampling time				0.3			μs
VREF	Reference volt	age			2.0		Vcc	V
VIA	Analog input ve	oltage			0		VREF	V

NOTES:

1. Referenced to VCC = AVCC = VREF = 3.3 to 5.5 V, VSS = AVSS = 0 V, -40 to 85°C unless otherwise specified.

2.  $\phi$ AD frequency must be 10 MHz or less.

When sample & hold is disabled, φAD frequency must be 250 kHz or more in addition to a limit of NOTE 2.
 When sample & hold is enabled, φAD frequency must be 1 MHz or more in addition to a limit of NOTE 2.

Table 5.7 D/A conversion Characteristics (1)

Symbol	Parameter	Measuring Condition	Standard			Unit
		Measuring Condition	Min.	Тур.	Max.	Onit
-	Resolution				8	Bits
-	Absolute accuracy				1.0	%
tsu	Setup time				3	μs
Ro	Output resistance		4	10	20	kΩ
IVREF	Reference power supply input current	(NOTE 2)			1.5	mA

NOTES:

1. Referenced to VCC = AVCC = VREF = 3.3 to 5.5 V, VSS = AVSS = 0 V, -40 to 85°C unless otherwise specified.

2. This applies when using one D/A converter, with the DAi register (i = 0, 1) for the unused D/A converter set to 00h. The resistor ladder of the A/D converter is not included. Also, the IVREF will flow even if VREF is disconnected by the ADCON1 register.

Sumbol	Parameter			Standard		Unit
Symbol			Min.	Тур.	Max.	
-	Programming and erasure end	urance <sup>(2)</sup>	100			cycle
-	Word program time (VCC = 5.0	• V)		25	200	μs
-	Lock bit program time			25	200	μs
-	Block erase time	4-Kbyte block		0.3	4	s
	(VCC = 5.0 V)	8-Kbyte block		0.3	4	s
		32-Kbyte block		0.5	4	s
		64-Kbyte block		0.8	4	S
-	Erase all unlocked blocks time				4 × n (3)	S
tps	Flash memory circuit stabilizati	on wait time			15	μs

## Table 5.8 Flash Memory Version Electrical Characteristics (1)

NOTES:

1. Referenced to VCC = 4.5 to 5.5 V, 3.0 to 3.6 V, Topr = 0 to  $60^{\circ}$ C unless otherwise specified.

2. Programming and erasure endurance refers to the number of times a block erase can be performed.

If the programming and erasure endurance is n (n = 100), each block can be erased n times. For example, if a 4-Kbyte block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one programming and erasure endurance. Data cannot be written to the same address more than once without erasing the block (rewrite prohibited).

3. n denotes the number of blocks to erase.

## Table 5.9 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at Topr = 0 to 60°C)

Flash Program, Erase Voltage	Flash Read Operation Voltage
VCC = 3.3 ± 0.3 V or 5.0 ± 0.5 V	VCC = 3.0 to 5.5 V

#### Table 5.10 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring	S	standar	d	Unit
Symbol		Condition	Min.	Тур.	Max.	Onit
td(P-R)	Time for internal power supply stabilization during powering-on	VCC = 3.0 to 5.5 V			2	ms
td(R-S)	STOP release time				150	μs
td(W-S)	Low power dissipation mode wait mode release time				150	μs

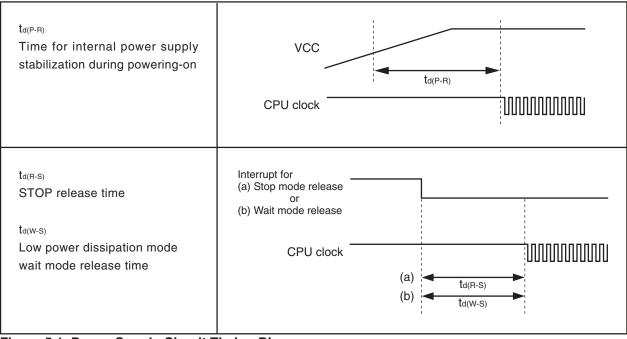


Figure 5.1 Power Supply Circuit Timing Diagram

## Timing Requirements VCC = 5 V(Referenced to VCC = 5 V, VSS = 0 V, at Topr = -40 to 85°C unless otherwise specified)

## Table 5.11 External Clock Input (XIN Input)

Symbol	Parameter	Stan	Unit	
Symbol	Falailletei	Min.	Max.	Unit
tc	External clock input cycle time	62.5		ns
t <sub>w(H)</sub>	External clock input HIGH pulse width	25		ns
tw(L)	External clock input LOW pulse width	25		ns
tr	External clock rise time		15	ns
tr	External clock fall time		15	ns

## Table 5.12 Memory Expansion Mode and Microprocessor Mode

Symbol	Parameter	Standard		Unit
Symbol	Falameter	Min.	Max.	Unit
tac1(RD-DB)	Data input access time (for setting with no wait)		(NOTE 1)	ns
tac2(RD-DB)	Data input access time (for setting with wait)		(NOTE 2)	ns
tac3(RD-DB)	Data input access time (when accessing multiplexed bus area)		(NOTE 3)	ns
tsu(DB-RD)	Data input setup time	40		ns
tsu(RDY-BCLK)	RDY input setup time	30		ns
tsu(HOLD-BCLK)	HOLD input setup time	40		ns
th(RD-DB)	Data input hold time	0		ns
th(BCLK-RDY)	RDY input hold time	0		ns
th(BCLK-HOLD)	HOLD input hold time	0		ns

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{\text{f(BCLK)}} - 45 \text{ [ns]}$$

2. Calculated according to the BCLK frequency as follows:

 $\frac{(n-0.5) \times 10^9}{f(BCLK)} - 45 \text{ [ns]}$  n is "2" for 1-wait setting, "3" for 2-wait setting and "4" for 3-wait setting.

3. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5) \times 10^9}{f(BCLK)} - 45 \text{ [ns]} \qquad n \text{ is "2" for 2-wait setting, "3" for 3-wait setting.}$$

## Timing Requirements VCC = 5 V (Referenced to VCC = 5 V, VSS = 0 V, at Topr = -40 to 85°C unless otherwise specified)

## Table 5.19 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Stan	Unit	
	Farameter	Min.	Max.	Unit
tc(TB)	TBiIN input cycle time (counted on one edge)	100		ns
t <sub>w(TBH)</sub>	TBiIN input HIGH pulse width (counted on one edge)	40		ns
tw(TBL)	TBiIN input LOW pulse width (counted on one edge)	40		ns
tc(TB)	TBiIN input cycle time (counted on both edges)	200		ns
t <sub>w(TBH)</sub>	TBiIN input HIGH pulse width (counted on both edges)	80		ns
tw(TBL)	TBiIN input LOW pulse width (counted on both edges)	80		ns

#### Table 5.20 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Stan	Unit	
		Min.	Max.	Unit
t <sub>c(TB)</sub>	TBIIN input cycle time	400		ns
tw(TBH)	TBiIN input HIGH pulse width	200		ns
tw(TBL)	TBiIN input LOW pulse width	200		ns

#### Table 5.21 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Stan	Unit	
	Farameter	Min.	Max.	
t <sub>c(TB)</sub>	TBiIN input cycle time	400		ns
tw(TBH)	TBiIN input HIGH pulse width	200		ns
tw(TBL)	TBiIN input LOW pulse width	200		ns

#### Table 5.22 A/D Trigger Input

Cumbol	Parametar	Stan	Linit	
Symbol	Parameter	Min.	Max.	Unit
tc(AD)	ADTRG input cycle time (trigger able minimum)	1000		ns
tw(ADL)	ADTRG input LOW pulse width	125		ns

## Table 5.23 Serial Interface

Symbol	Parameter	Stan	Unit	
		Min.	Max.	Unit
tc(CK)	CLKi input cycle time	200		ns
t <sub>w(CKH)</sub>	CLKi input HIGH pulse width	100		ns
tw(CKL)	CLKi input LOW pulse width	100		ns
td(C-Q)	TXDi output delay time		80	ns
th(C-Q)	TXDi hold time	0		ns
tsu(D-C)	RXDi input setup time	70		ns
th(C-D)	RXDi input hold time	90		ns

#### Table 5.24 External Interrupt INTi Input

Symbol	Symbol Parameter	Stan	Unit	
Symbol		Min.	Max.	Unit
t <sub>w(INH)</sub>	INTi input HIGH pulse width	250		ns
t <sub>w(INL)</sub>	INTi input LOW pulse width	250		ns

## Switching Characteristics VCC = 5 V(Referenced to VCC = 5 V, VSS = 0 V, at Topr = -40 to 85 °C unless otherwise specified)

Symbol	Parameter	Measuring	Standard		Unit
Symbol	Falalletei	Condition	Min.	Max.	Onit
td(BCLK-AD)	Address output delay time	Figure 5.2		25	ns
th(BCLK-AD)	Address output hold time (in relation to BCLK)		4		ns
th(RD-AD)	Address output hold time (in relation to RD)		0		ns
th(WR-AD)	Address output hold time (in relation to WR)		(NOTE 1)		ns
td(BCLK-CS)	Chip select output delay time			25	ns
th(BCLK-CS)	Chip select output hold time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE signal output delay time			15	ns
th(BCLK-ALE)	ALE signal output hold time		-4		ns
td(BCLK-RD)	RD signal output delay time			25	ns
th(BCLK-RD)	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			25	ns
th(BCLK-WR)	WR signal output hold time		0		ns
td(BCLK-DB)	Data output delay time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data output hold time (rin relation to BCLK) (3)		4		ns
td(DB-WR)	Data output delay time (in relation to WR)		(NOTE 2)		ns
th(WR-DB)	Data output hold time (in relation to WR) (3)		(NOTE 1)		ns
td(BCLK-HLDA)	HLDA output delay time			40	ns

#### Table 5.26 Memory Expansion Mode and Microprocessor Mode (for 1- to 3-wait setting and external area access)

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10 [ns]$$

2. Calculated according to the BCLK frequency as follows:

 $\frac{(n-0.5) \times 10^9}{f(BCLK)} - 40 \text{ [ns]}$ 

n is "1" for 1-wait setting, "2" for 2-wait setting and "3" for 3-wait setting. When n = 1, f(BCLK) is 12.5 MHz or less.

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.

Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.

Hold time of data bus is expressed in

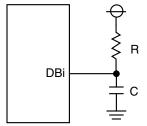
 $t = -CR \times ln (1 - V_{OL} / V_{CC})$ 

by a circuit of the right figure.

For example, when  $V_{OL} = 0.2 V_{CC}$ , C = 30 pF,

R =1 k $\Omega$ , hold time of output "L" level is

t =  $-30 \text{ pF} \times 1 \text{ k}\Omega \times \text{ln} (1 - 0.2 \text{ Vcc} / \text{Vcc}) = 6.7 \text{ ns.}$ 



## Table 5.28 Electrical Characteristics (1)

## VCC = 3.3 V

		Character		1	0	tandar	<u>-d</u>	
Symbol		Pa	rameter	Measuring Condition	Min.	Typ.	Max.	Unit
Vон	HIGH output voltage	P3_0 to P P6_0 to P6 P8_6, P8_7	0_7, P1_0 to P1_7, P2_0 to P2_7, 3_7, P4_0 to P4_7, P5_0 to P5_7, _7, P7_0, P7_2 to P7_7, P8_0 to P8_4, 7, P9_0, P9_2 to P9_7, P10_0 to P10_7, 11_7, P12_0 to P12_7, P13_0 to P13_7, 14_1		Vcc-0.5		Vcc	V
Vон	HIGH output voltage	XOUT	HIGHPOWER LOWPOWER	Іон = -0.1 mA Іон = -50 µA	Vcc-0.5 Vcc-0.5		Vcc Vcc	V
	HIGH output voltage	XCOUT	HIGHPOWER LOWPOWER	With no load applied With no load applied		2.5 1.6		V
Vol	LOW output voltage	P3_0 to P P6_0 to P P8_6, P8_	0_7, P1_0 to P1_7, P2_0 to P2_7, 3_7, P4_0 to P4_7, P5_0 to P5_7, 6_7, P7_0 to P7_7, P8_0 to P8_4, _7, P9_0 to P9_7, P10_0 to P10_7, 11_7,P12_0 to P12_7, P13_0 to P13_7, '14_1				0.5	V
Vol	LOW output voltage	XOUT	HIGHPOWER LOWPOWER	lo∟ = 0.1 mA lo∟ = 50 μA			0.5 0.5	V
	LOW output voltage	XCOUT	HIGHPOWER LOWPOWER	With no load applied With no load applied		0		V
V⊤+-V⊤-	Hysteresis	INTO to IN SCL0 to S TA0OUT	IV, TAOIN to TA4IN, TBOIN to TB5IN,         IT8, NMI, ADTRG, CTS0 to CTS2,         CL2, SDA0 to SDA2, CLK0 to CLK6,         to TA4OUT, KI0 to KI3,         RXD2, SIN3 to SIN6		0.2		0.8	V
V⊤+-V⊤-	Hysteresis	RESET	,		0.2		1.8	V
Ін	HIGH input current	P3_0 to P P6_0 to P P9_0 to P11_0 to P13_0 to XIN, RES	0_7, P1_0 to P1_7, P2_0 to P2_7, 3_7, P4_0 to P4_7, P5_0 to P5_7, 6_7, P7_0 to P7_7, P8_0 to P8_7, P9_7, P10_0 to P10_7, P11_7, P12_0 to P12_7, 0 P13_7, P14_0, P14_1, SET, CNVSS, BYTE				4.0	μΑ
lι	LOW input current	P3_0 to P P6_0 to P P9_0 to F P11_0 to P13_0 to	0_7, P1_0 to P1_7, P2_0 to P2_7, 3_7, P4_0 to P4_7, P5_0 to P5_7, 6_7, P7_0 to P7_7, P8_0 to P8_7, P9_7, P10_0 to P10_7, P11_7, P12_0 to P12_7, P13_7, P14_0, P14_1, SET, CNVSS, BYTE				-4.0	μA
Rpullup	Pull-up resistance	P3_0 to P P6_0 to P P8_4, P8 P10_0 to	0_7, P1_0 to P1_7, P2_0 to P2_7, 3_7, P4_0 to P4_7, P5_0 to P5_7, 6_7, P7_0, P7_2 to P7_7, P8_0 to _6, P8_7, P9_0, P9_2 to P9_7, P10_7, P11_0 to P11_7, P12_7, P13_0 to P13_7, '14_1		50	100	500	kΩ
Rfxin	Feedback resis		XIN			3.0		MΩ
Rfxcin	Feedback resis		XCIN			25		MΩ
VRAM	RAM retention	voltage		At stop mode	2.0			V

NOTES:

1. Referenced to VCC = 3.0 to 3.6 V, VSS = 0 V at Topr = -40 to 85°C, f(BCLK) = 24 MHz unless otherwise specified.

2. P11 to P14, INT6 to INT8, CLK5, CLK6, SIN5, and SIN6 are only in the 128-pin version.

## Timing Requirements VCC = 3.3 V (Referenced to VCC = 3.3 V, VSS = 0 V, at Topr = -40 to 85°C unless otherwise specified)

### Table 5.31 Timer A Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Stan	Unit	
		Min.	Max.	Unit
tc(TA)	TAIIN input cycle time	150		ns
tw(TAH)	TAIIN input HIGH pulse width	60		ns
tw(TAL)	TAIIN input LOW pulse width	60		ns

#### Table 5.32 Timer A Input (Gating Input in Timer Mode)

Symbol	Parameter	Stan	Unit	
		Min.	Max.	
tc(TA)	TAIIN input cycle time	600		ns
tw(TAH)	TAIIN input HIGH pulse width	300		ns
tw(TAL)	TAiIN input LOW pulse width	300		ns

### Table 5.33 Timer A Input (External Trigger Input in One-shot Timer Mode)

Symbol	Parameter	Stan	Unit	
		Min.	Max.	Unit
t <sub>c(TA)</sub>	TAIIN input cycle time	300		ns
tw(TAH)	TAIIN input HIGH pulse width	150		ns
tw(TAL)	TAIIN input LOW pulse width	150		ns

#### Table 5.34 Timer A Input (External Trigger Input in Pulse Width Modulation Mode)

Symbol	Parameter	Stan	Unit	
		Min.	Max.	Unit
t <sub>w(TAH)</sub>	TAIIN input HIGH pulse width	150		ns
tw(TAL)	TAIIN input LOW pulse width	150		ns

#### Table 5.35 Timer A Input (Counter Increment/decrement Input in Event Counter Mode)

Symbol	Parameter	Stan	Unit	
Symbol		Min.	Max.	Unit
t <sub>c(UP)</sub>	TAiOUT input cycle time	3000		ns
tw(UPH)	TAIOUT input HIGH pulse width	1500		ns
tw(UPL)	TAiOUT input LOW pulse width	1500		ns
tsu(UP-TIN)	TAIOUT input setup time	600		ns
th(TIN-UP)	TAiOUT input hold time	600		ns

#### Table 5.36 Timer A Input (Two-phase Pulse Input in Event Counter Mode)

Symbol	Parameter	Stan	Unit	
		Min.	Max.	Unit
tc(TA)	TAIIN input cycle time	2		μs
tsu(TAIN-TAOUT)	TAiOUT input setup time	500		ns
tsu(taout-tain)	TAIIN input setup time	500		ns

### **Switching Characteristics**

## VCC = 3.3 V

(Referenced to VCC = 3.3 V, VSS = 0 V, at Topr = -40 to 85 °C unless otherwise specified)

Symbol	Parameter	Measuring	Standard		Unit
Symbol	Parameter	Condition	Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	Figure 5.11		50	ns
$t_{h(BCLK-AD)}$	Address output hold time (in relation to BCLK)		4		ns
th(RD-AD)	Address output hold time (in relation to RD)		(NOTE 1)		ns
th(WR-AD)	Address output hold time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			50	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (in relation to BCLK)		4		ns
th(RD-CS)	Chip select output hold time (in relation to RD)		(NOTE 1)		ns
th(WR-CS)	Chip select output hold time (in relation to WR)	_	(NOTE 1)		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			40	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time	-		40	ns
$t_{h(BCLK-WR)}$	WR signal output hold time	-	0		ns
td(BCLK-DB)	Data output delay time (in relation to BCLK)			50	ns
$t_{h(BCLK-DB)}$	Data output hold time (in relation to BCLK)		4		ns
$t_{d(DB-WR)}$	Data output delay time (in relation to WR)		(NOTE 2)		ns
$t_{h(WR-DB)}$	Data output hold time (in relation to WR)		(NOTE 1)		ns
$t_{d(BCLK-HLDA)}$	HLDA output delay time			40	ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time (in relation to BCLK)			25	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time (in relation to BCLK)		-4		ns
$t_{d(AD-ALE)}$	ALE signal output delay time (in relation to Address)		(NOTE 3)		ns
th(ALE-AD)	ALE signal output hold time (rin relation to Address)		(NOTE 4)		ns
td(AD-RD)	RD signal output delay from the end of Address		0		ns
td(AD-WR)	WR signal output delay from the end of Address		0		ns
$t_{dZ(RD-AD)}$	Address output floating start time			8	ns

## Table 5.45 Memory Expansion Mode and Microprocessor Mode (for 2- to 3-wait setting, external area access and multiplexed bus selection)

NOTES:

1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 10 \text{ [ns]}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{(n-0.5) \times 10^{\circ}}{f(BCLK)} - 50 \text{ [ns]} \quad n \text{ is "2" for 2-wait setting, "3" for 3-wait setting.}$$

3. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{f(BCLK)} - 40 \text{ [ns]}$$

4. Calculated according to the BCLK frequency as follows:

$$\frac{0.5 \times 10^9}{\text{f(BCLK)}} - 15 \text{ [ns]}$$

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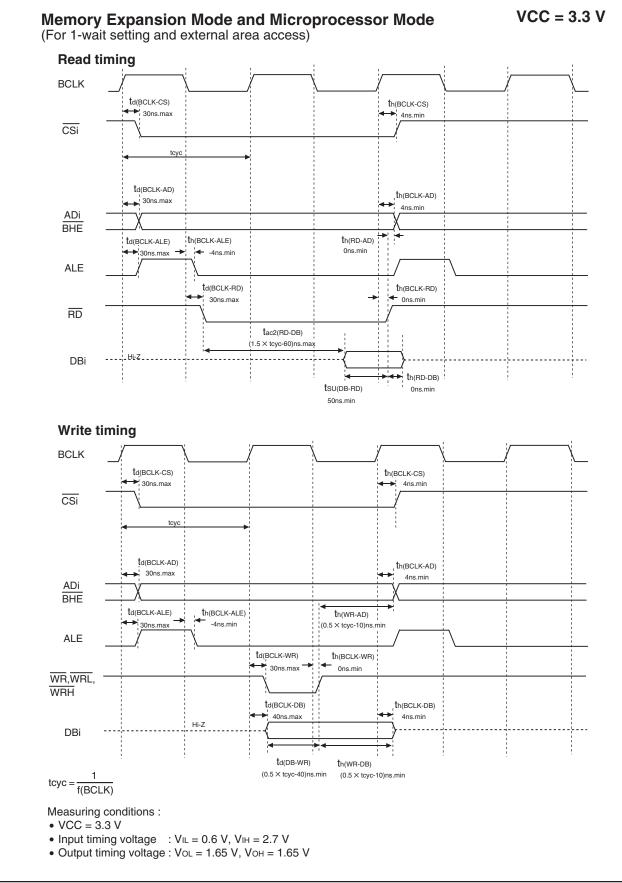


Figure 5.15 Timing Diagram (4)

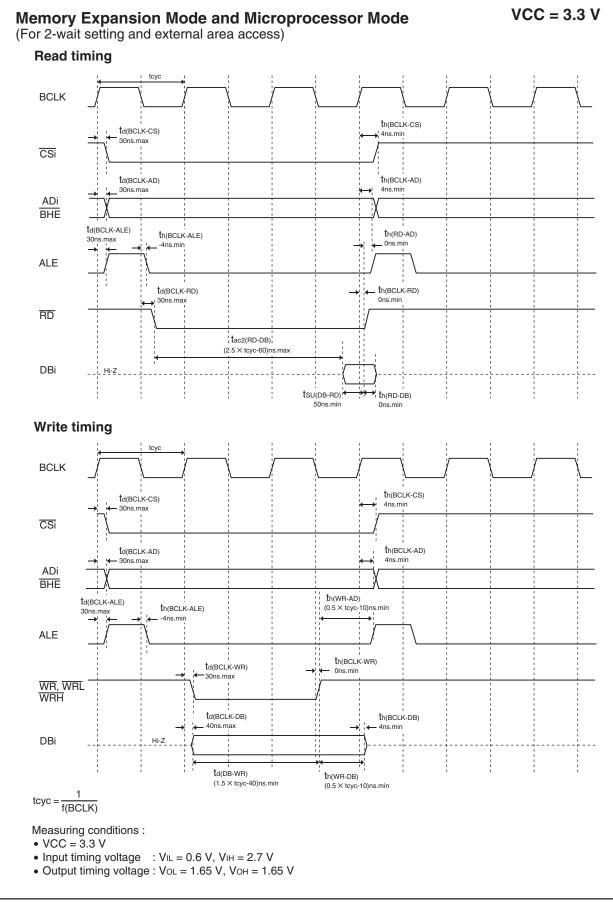


Figure 5.16 Timing Diagram (5)

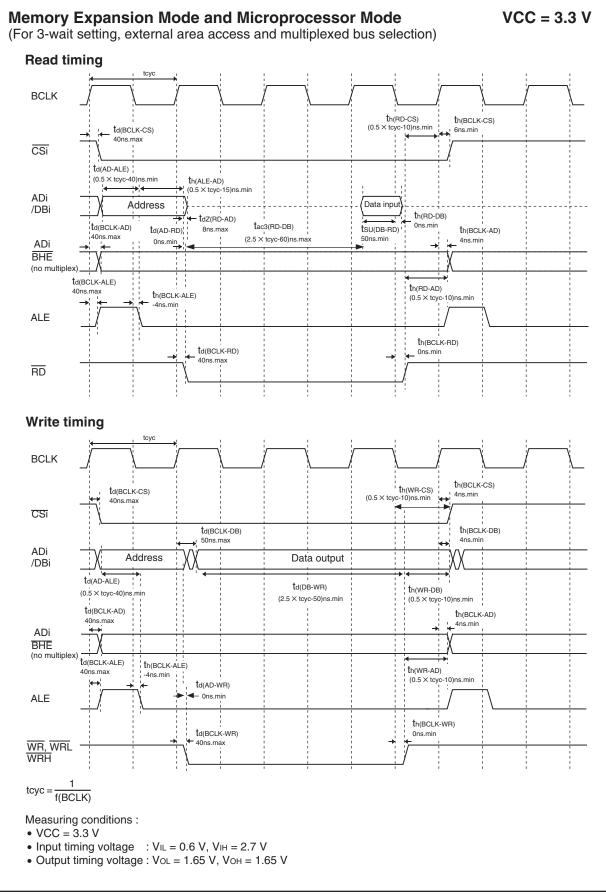


Figure 5.19 Timing Diagram (8)